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The Honorable Commissioner of Patents & Trademarks
Washington, D.C. 20231

Dear Sir:

IN THE CLAIMS:

Please amend claim 1, as follows:

1. (Three Times Amended) A semiconductor device including both a large-diameter contact hole having an aspect ratio of not greater than 2 and a small-diameter contact hole having an aspect ratio of greater than 2 formed to penetrate through an insulator film formed on a conductive portion to reach said conductive portion, said small-diameter contact hole being completely filled with a plug of a refractory conductive material, and said large-diameter contact hole being partly filled by said refractory conductive material which covers a sidewall surface of said large-diameter contact hole to below the upper end of said large-diameter contact hole by a